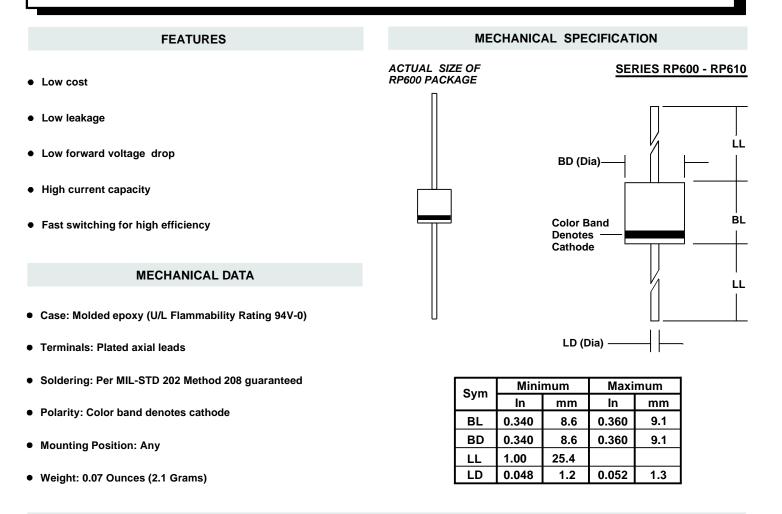


## **6 AMP FAST RECOVERY SILICON DIODES**



## **MAXIMUM RATINGS & ELECTRICAL CHARACTERISTICS**

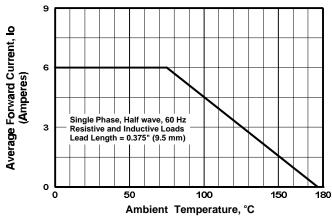
Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive loads, derate current by 20%.

PARAMETER (TEST CONDITIONS)	SYMBOL	RATINGS							UNITS
Series Number		RP600	RP601	RP602	RP604	RP606	RP608	RP610	
Maximum DC Blocking Voltage	Vrм	50	100	200	400	600	800	1000	VOLTS
Maximum RMS Voltage	Vrms	35	70	140	280	420	560	700	
Maximum Peak Recurrent Reverse Voltage	Vrrm	50	100	200	400	600	800	1000	
Average Forward Rectified Current @ TA = 60 °C, Lead length = 0.375 in. (9.5 mm)	lo	6							AMPS
Peak Forward Surge Current ( 8.3 mSec single half sine wave superimposed on rated load)	IFSM	300							
Maximum Forward Voltage at 6 Amps DC	Vfm	1.3							VOLTS
Maximum Reverse Recovery Time (IF=0.5A, IR=1A, IRR=0.25A)	Trr	150			250	500 (Note 3)		nS	
Maximum Average DC Reverse Current@ TA = 25°CAt Rated DC Blocking Voltage@ TA = 100°C	Iгм	10 200							μΑ
Typical Junction Capacitance (Note 2)	CJ	100						pF	
Operating and Storage Temperature Range	TJ, TSTG	-65 to +175						°C	

NOTES: (1) Lead length = 0.375 in. (9.5 mm) (2) Measured at 1MHz & applied reverse voltage of 4 volts (3) 300 nS avaiable - consult with factory

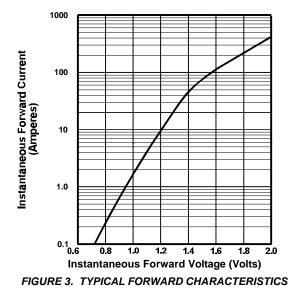


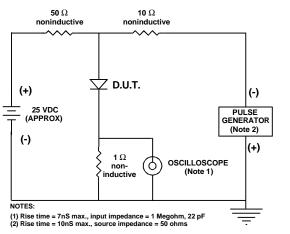
## 6 AMP FAST RECOVERY DIODES

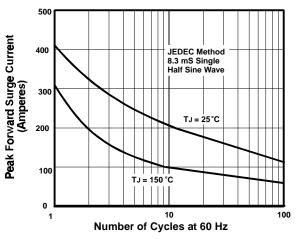


## RATING & CHARACTERISTIC CURVES FOR SERIES RP600 - RP610











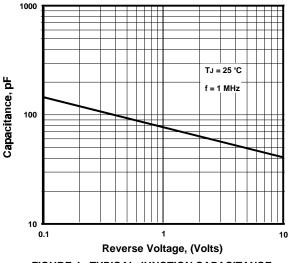


FIGURE 4. TYPICAL JUNCTION CAPACITANCE

4.97bfsdp60

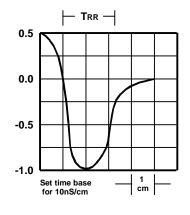


FIGURE 5. REVERSE RECOVERY TEST SETUP AND TIME CHARACTERISTIC